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(54) **METHOD FOR MODIFICATION OF BUILT IN POTENTIAL OF DIODES**

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See application file for complete search history.

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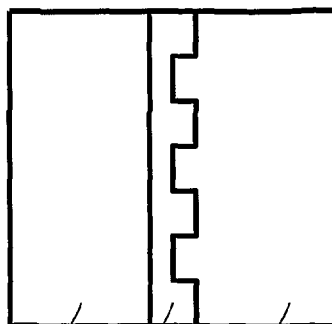
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(57) **ABSTRACT**

In broad terms the present invention is a semiconductor junction comprising a first material (102) and a second material (104), in which a surface of one or both of the junction materials has a periodically repeating structure that causes electron wave interference resulting in a change in the way electron energy levels within the junction are distributed.

18 Claims, 1 Drawing Sheet



106 104 102